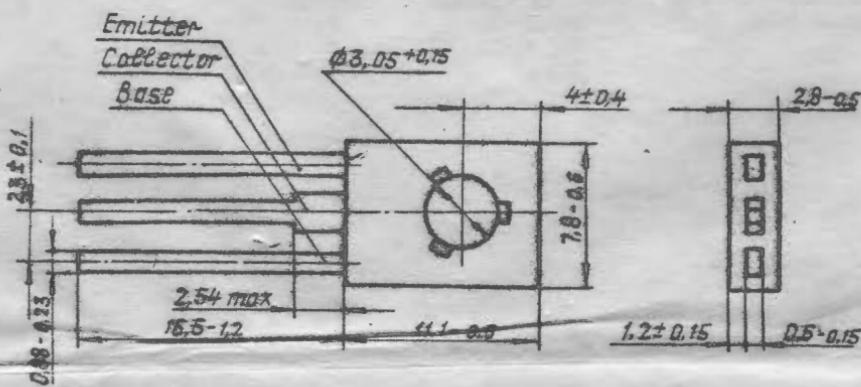


L A B E L

PNP BD136, BD138, BD140

PLASTIC MEDIUM POWER SILICON TRANSISTORS



Case TO-126

MAXIMUM RATINGS

Rating	Symbol	BD136	BD138	BD140	Unit
Collector-Emitter Voltage	Vceo	45	60	80	V
Collector-Base Voltage	Vcbo	45	60	100	V
Emitter-Base Voltage	Veb	—	5	—	V
Collector Current-Continuous	Ic	—	1,5	—	A
Base Current	Ib	—	0,5	—	A
Total Device Dissipation @ $T_c=25^\circ C$	Pd	—	12,5	—	Watts
Junction Temperature	Tj	—	150	—	$^\circ C$

ELECTRICAL CHARACTERISTICS (Tc=25°C)

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Sustaining Voltage (Ic= 50mA, Ib=0)	Vceo(sus)			V
BD136		45	-	
BD138		60	-	
BD140		80	-	
Collector Cutoff Current (Vcb=30V, Ie=0)	Icbo	-	0,1	μA
Emitter Cutoff Current (Vbe=5V, Ic=0)	Ieb0	-	10	μA
DC Current Gain (Ic= 5mA, Vce=2V) (Ic=150mA, Vce=2V)	hFE			-
BDXXX		25	-	
BDXXX-06		40	250	
BDXXX-10		40	100	
BDXXX-16		63	160	
(Ic=0,5A, Vce=2V)		100	250	
		25	-	
Collector-Emitter Saturation Voltage (Ic=0,5A, Ib=50mA)	Vce(sat)	-	0,5	V
Base-Emitter ON Voltage (Ic=0,5A, Vce=2V)	Vbe(on)	-	1	V